Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A silicon carbide epitaxial wafer which is formed on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an α-type crystal structure, said silicon carbide epitaxial wafer being formed on a {0001} C face of the substrate and said substrate being a silicon carbide substrate having a 4H crystal structure.

Claims 2-5 (canceled).

Claim 6 (currently amended): A manufacturing method of a silicon carbide epitaxial wafer, ~~wherein silicon carbide is~~ comprising the steps of:

cleansing a surface of a substrate with a mixed gas of hydrogen gas and propane gas at 1400°C to 1600°C;

epitaxially ~~grown~~ growing silicon carbide on a {0001} C face of the substrate that is less than 1° off from the {0001} surface of silicon carbide having an α-type crystal structure, the substrate being a silicon carbide substrate having a 4H crystal structure; and

during said epitaxially growing step, using a source gas of silane and propane having a compositional ratio of C and Si of 1 or less and a growth pressure of 250mbar or less.

Claim 7-16 (canceled).

Claim 17 (currently amended): A silicon carbide epitaxial wafer according to claim [16] 1, wherein said silicon carbide epitaxial wafer has a flat surface.

Claim 18 (previously presented): A silicon carbide epitaxial wafer according to claim 17, further comprising a semiconductor device formed on said silicon carbide epitaxial wafer.

Claims 19-20 (canceled).

Claim 21 (previously presented): A silicon carbide epitaxial wafer according to claim 1, further comprising a semiconductor device formed on said silicon carbide epitaxial wafer.

Claims 22-23 (canceled).

Claim 24 (previously presented): A method according to claim 6, wherein said substrate has a surface step with a height of 1nm or less.

Claims 25-27 (canceled).

Claim 28 (currently amended): A silicon carbide epitaxial wafer prepared by a process comprising the steps of:

cleansing a surface of a substrate with a mixed gas of hydrogen gas and propane gas at 1400°C to 1600°C;

epitaxially growing silicon carbide on a {0001} C face of the substrate that is less than 1° off from the {0001} surface of silicon carbide having an α-type crystal structure, said substrate being a silicon carbide substrate having a 4H crystal structure; and

during said epitaxially growing step, using a source gas of silane and propane having a compositional ratio of C and Si of 1 or less and a growth pressure of 250mbar or less.

Claims 29-30 (canceled).

Claim 31 (previously presented): A silicon carbide epitaxial wafer according to claim 28, wherein a semiconductor device is formed on said silicon carbide epitaxial wafer.